

~~A~~
Sub B1 (contd)
ii) depositing a second amount of metal on said seed layer at a substrate temperature and power[, providing] that are sufficient to (i) inhibit formation of filamentous metal phases having a resistivity greater than that of said metal, and (ii) provide a metal diffusion rate and a [second] metal deposition rate sufficient to inhibit void formation in an opening having an aspect ratio of at least [1.0] 2.0; and

~~iii) depositing a third amount of metal on said second amount of metal.~~

Please add new claims 22-24 as follows:

~~A~~
Sub B2
22. A method of forming a layer of aluminum-containing metal on a substrate, comprising:

i) depositing a first amount of a metal comprising aluminum on a seed layer of the metal, said seed layer being sufficient to cover a substrate surface comprising titanium, at a substrate power sufficient to inhibit formation of a phase of $TiAl_3$ having a resistivity greater than that of said metal; and

~~ii) depositing a second amount of metal on said first amount of metal.~~

A2
23. The method of claim 22, wherein said first amount of said metal is deposited at a metal diffusion rate and a metal deposition rate sufficient to inhibit void formation in an opening having an aspect ratio of at least 2.0.

~~24. A method of forming a layer of aluminum-containing metal on a substrate, comprising:~~

~~Sub B3
i) depositing a first amount of a metal comprising aluminum on a seed layer of the metal, said seed layer being sufficient to cover a substrate surface, at a substrate power sufficient to inhibit formation of a phase containing said metal having a resistivity greater than that of said metal and at a metal diffusion rate and a metal deposition rate sufficient to inhibit void formation~~